

“SuperSOT” SOT23 NPN SILICON POWER DARLINGTON TRANSISTOR

FMMT634

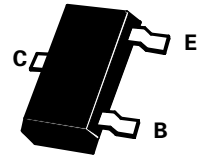
ISSUE 1 – APRIL 97

FEATURES

- * **625mW POWER DISSIPATION**
- * Highest current capability SOT23 Darlington
- * Very high hFE - specified at 2A (5K minimum)
- typically 600 at 5A

COMPLEMENTARY TYPE – FMMT734

PARTMARKING DETAIL – 634



SOT23

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	120	V
Collector-Emitter Voltage	V_{CEO}	100	V
Emitter-Base Voltage	V_{EBO}	12	V
Peak Pulse Current	I_{CM}	5	A
Continuous Collector Current	I_C	900	mA
Power Dissipation	P_{tot}	625	mW
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150	°C

* Maximum power dissipation is calculated assuming that the device is mounted on a ceramic substrate measuring 15x15x0.6mm.

**Measured under pulsed conditions. Pulse width=300µs. Duty cycle ≤ 2%.

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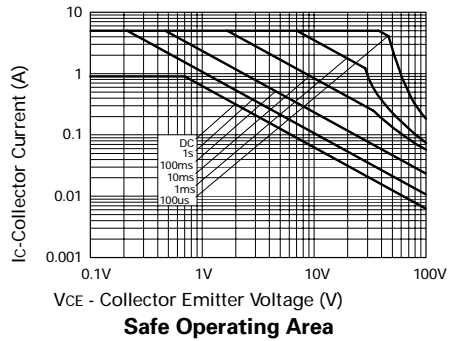
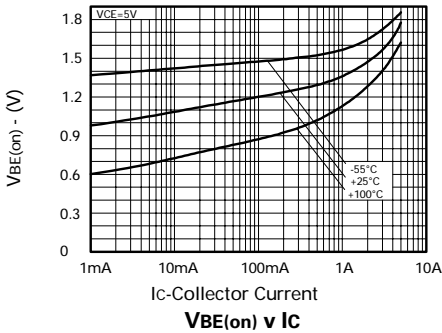
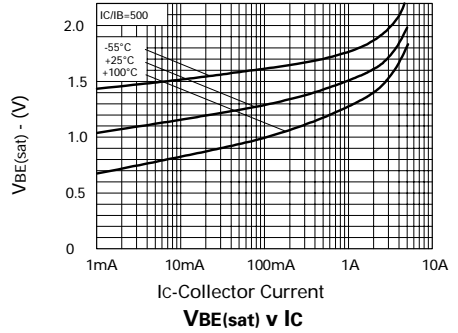
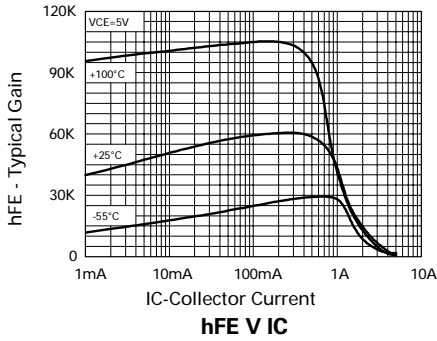
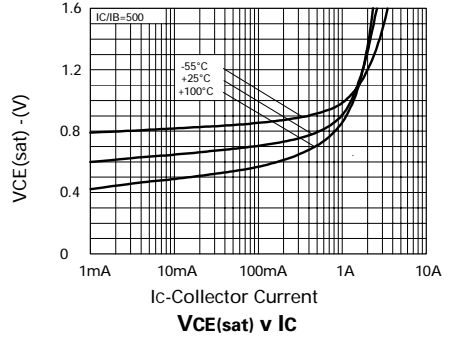
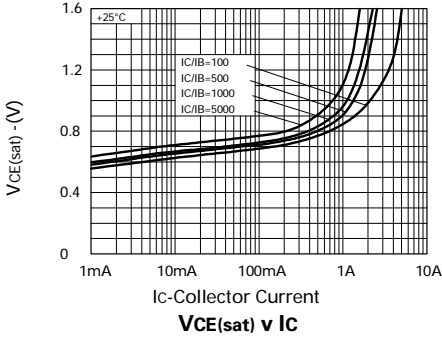
ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	120	170		V	$I_C=100\mu\text{A}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	100	115		V	$I_C=10\text{mA}^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	12	16		V	$I_E=100\mu\text{A}$
Collector Cut-Off Current	I_{CBO}			10	nA	$V_{CB}=80\text{V}$
Emitter Cut-Off Current	I_{EBO}			10	nA	$V_{EB}=7\text{V}$
Collector Emitter Cut-Off Current	I_{CES}			100	nA	$V_{CES}=80\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		0.67 0.72 0.75 0.82 0.68 0.85	0.75 0.80 0.85 0.93 — 0.96	V	$I_C=100\text{mA}, I_B=1\text{mA}^*$ $I_C=250\text{mA}, I_B=1\text{mA}^*$ $I_C=500\text{mA}, I_B=5\text{mA}^*$ $I_C=900\text{mA}, I_B=5\text{mA}^*$ $I_C=900\text{mA}, I_B=5\text{mA}^* \dagger$ $I_C=1\text{A}, I_B=5\text{mA}^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		1.5	1.65	V	$I_C=1\text{A}, I_B=5\text{mA}^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		1.33	1.5	V	$I_C=1\text{A}, V_{CE}=5\text{V}^*$
Static Forward Current Transfer Ratio	h_{FE}	20K 15K 5K	50K 60K 40K 14K 600 24K			$I_C=10\text{mA}, V_{CE}=5\text{V}^*$ $I_C=100\text{mA}, V_{CE}=5\text{V}^*$ $I_C=1\text{A}, V_{CE}=5\text{V}^*$ $I_C=2\text{A}, V_{CE}=5\text{V}^*$ $I_C=5\text{A}, V_{CE}=5\text{V}^*$ $I_C=1\text{A}, V_{CE}=2\text{V}^*$
Transition Frequency	f_T		140		MHz	$I_C=50\text{mA}, V_{CE}=10\text{V}$ $f=100\text{MHz}$
Output Capacitance	C_{obo}		9	20	pF	$V_{CB}=10\text{V}, f=1\text{MHz}$
Turn-On Time	$t_{(on)}$		290		ns	$I_C=500\text{mA}$ $V_{CC}=20\text{V}$
Turn-Off Time	$t_{(off)}$		2.4		μs	$I_B=\pm 1\text{mA}$

*Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$.

$\dagger T_J=150^{\circ}\text{C}$

TYPICAL CHARACTERISTICS





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